

SANYO

No.3166

2SK1237

N-Channel GaAs MES FET

12GHz-Band Local Oscillator,
Amplifier Applications**Features**

- Ceramic package
- High gain
- Adoption of high reliable protection film

Absolute Maximum Ratings at Ta = 25°C

			unit
Drain to Source Voltage	V _{DS}	5	V
Gate to Source Voltage	V _{GS}	-5	V
Drain Current	I _D	70	mA
Allowable Power Dissipation	P _D	270	mW
Junction Temperature	T _J	150	°C
Storage Temperature	T _{stg}	-65 to +150	°C

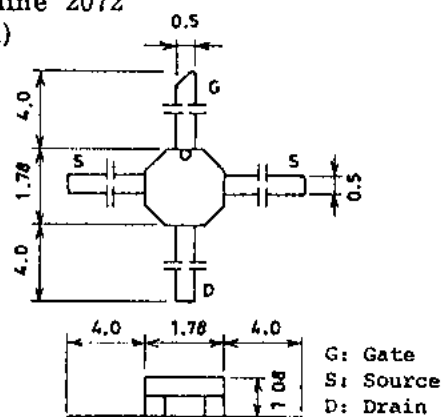
Electrical Characteristics at Ta = 25°C

		min	typ	max	unit
Gate to Drain Breakdown Voltage	V _{(BR)GDS} I _G = -10μA, V _{DS} = 0V	-5			V
Gate Cutoff Current	I _{GSS} V _{GS} = -3V, V _{DS} = 0V			-10	μA
Drain Current	I _{DSS} V _{DS} = 3V, V _{GS} = 0V	20	50	80	mA
Gate to Source Cutoff Voltage	V _{GS(off)} V _{DS} = 3V, I _D = 100μA	-0.5		-3	V
Forward Transfer Admittance	y _{fs} V _{DS} = 3V, I _D = 10mA	30	40		mS
Noise Figure	NF V _{DS} = 3V, I _D = 10mA, f = 12GHz		1.8		dB
Associated Gain	Ga V _{DS} = 3V, I _D = 10mA, f = 12GHz		7		dB
Maximum Available Power Gain	MAG V _{DS} = 3V, I _D = 10mA, f = 12GHz		10		dB
Maximum Oscillation Frequency	f _{max} V _{DS} = 3V, I _D = 30mA		70		GHz

The application circuit diagrams and circuit constants herein are included as an example and provide no guarantee for designing equipment to be mass-produced.

The information herein is believed to be accurate and reliable. However, no responsibility is assumed by SANYO for its use; nor for any infringements of patents or other rights of third parties which may result from its use.

Case Outline 2072
(unit : mm)



Specifications and information herein are subject to change without notice.

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